### **Supporting Information**

# Liquid Crystal Circularly Polarised TADF Emitters for High Efficiency, Solution-Processable Organic Light-Emitting Diodes

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#### **General information**

Unless other noted, all reagents used in the experiments were purchased from commercial sources without further purification. For column chromatography, silica gel with  $200 \sim 300$  mesh was used.

In order to determine the structure of the compound, <sup>1</sup>H NMR was acquired using a Bruker Dex-300/400/500 NMR instrument using CD<sub>2</sub>Cl<sub>2</sub> as a solvent. Mass spectra (MS) were recorded on a Bruker Autoflex MALDI-TOF instrument using benzhydrol as a matrix. Thermogravimetric analysis (TGA) was detected with a NETZSCH STA449 at a 20°C/min heating rate under N2 atmosphere. UV-vis absorption spectra were recorded on a Shimadzu UV-1650PC. Steady-state fluorescence/phosphorescence spectra PL spectra were carried out by using Edinburgh FLS1000 fluorescence spectrophotometer. The CPL and CD spectra of the compound were measured in the film state, and the films for chiroptical property were prepared by drip film method. The preparation process for the films is as follows: the compound was dissolved in dichloromethane and slowly added to the quartz glass substrate, and the pure film was obtained after drying. CD and CPL spectra were measured on JASCO J-1500 and JASCO CPL-200 spectrophotometers, respectively. The film thickness was measured by Dektak-XT probe surface profiler, and the film thickness is about 30 nm. In this paper, the circular polarisation spectrum of the compound in the film state was tested. The films for chiroptical property were fabricated as regular neat films in a drop film manner. The sample preparation process was as follows: the compound was dissolved in dichloromethane and slowly added to the quartz glass substrate, and the pure film

was obtained after drying. Polarised optical microscopy (POM) was carried out using an Olympus BX50 Optical Microscope equipped with a Linkam Scientific LTS350 heating stage, Linkam LNP2 cooling pump, and Linkam TMS92 controller. Small angle X-ray scattering was performed using a Bruker D8 Discover equipped with a bespoke temperature-controlled, bored graphite rod furnace, custom built at the University of York. The radiation used was  $CuK_a$  ( $\lambda = 0.154056$  nm) from a 1 µs microfocus source. Diffraction patterns were recorded on a 2048 x 2048 pixel Bruker VANTEC 500 area detector set at a distance of 121 mm from the sample. Samples were filled into 0.9 mm capillary tubes.

Solution-processed device: Poly(styrene sulfonate) (PEDOT: PSS) was purchased from Xi'an Polymer Light Technology Corp. (1,3,5-tris(*m*-pyrid-3-ylphenyl)benzene) (TmPyPB), and LiF were purchased from Lumtec. All commercially available reagents were used without further purification. In devices, PEDOT: PSS was used as hole injection material. TmPyPB and LiF were used as electron transport and injection materials, respectively. ITO (indium tin oxide) and Al (aluminium) were used as anode and cathode materials, respectively. The substrates were successively cleaned with isopropyl alcohol, acetone, detergent, deionised water, and isopropyl alcohol in an ultrasonic bath and then dried overnight in the oven. The substrates pre-treated by oxygen plasma to increase the work function of the ITO film. Then, 40 nm-thick PEDOT: PSS was spin-coated onto the ITO substrates at 3200 rpm for 30 s and annealed at 150 °C for 15 minutes. And then emissive layer was spin-coated and annealed at 60 °C for 30 minutes using a precursor containing different materials codissolved in chlorobenzene or toluene. The films of TmPyPB, LiF and aluminium were prepared by thermal evaporation under a vacuum of  $1 \times 10^{-4}$  Pa. Each sample has an active area of 0.04 cm<sup>2</sup>. The thermally evaporated deposition rates were 0.6-1 Å s<sup>-1</sup> for the TmPyPB, 0.1 Å s<sup>-1</sup> for LiF and 1.5-1.8 Å s<sup>-1</sup> for the Al electrode, respectively. The current-voltage-luminance (*J-V-L*) characteristics and the electroluminescence spectra of the devices were obtained simultaneously by using a spectroradiometer (PR735) and a Keithley 2400 SourceMeter unit under ambient atmosphere at room temperature.

#### Synthetic procedures and characterisation data

Synthetic procedures



Scheme S1. R/S-4 synthesis route.

Synthesis of Compound 1: R/S 6,6' -dibromo-[1,1'-binaphthalene]-2, 2,2' -diol (0.5 g, 1.1 mmol), 2,3,5,6-tetrafluorophenyl dimethyl nitrile (0.2 g, 1.1 mmol), potassium carbonate (0.3 g, 0.3 g) were added to a 50 mL single-mouth bottle. 2.3 mmol), 8 mL anhydrous *N*,*N*-dimethylformamide, the reaction system was replaced with nitrogen for three times and reacted at room temperature for 12 hours. The monitoring reaction was complete. Carbazole (0.5 g, 2.8 mmol) and potassium carbonate (0.8 g, 5.7 mmol) were added again, and nitrogen was replaced again and the reaction was continued at room temperature for 12 hours. After the reaction, water was added and extracted with CH<sub>2</sub>Cl<sub>2</sub> (3×15 mL), washed with water (3×30 mL), dried with anhydrous magnesium sulfate, filtered and collected the filtrate, and the solvent was removed with a rotary evaporator. Using PE and CH<sub>2</sub>Cl<sub>2</sub> (volume ratio 1:1) as eluent, 0.56 g of white solid was obtained by column chromatography, and the yield was 55%. <sup>1</sup>H NMR (400 MHz,

CD<sub>2</sub>Cl<sub>2</sub>) δ (ppm) 8.19 (d, *J* = 1.9 Hz, 2H), 8.05 (d, *J* = 8.9 Hz, 2H), 7.76-7.68 (m, 4H), 7.63 (d, *J* = 7.7 Hz, 2H), 7.49 (dd, *J* = 9.0, 2.0 Hz, 2H), 7.31 (d, *J* = 9.0 Hz, 2H), 7.22-7.17 (m, 2H), 7.15-7.09 (m, 4H), 6.93 (td, *J* = 7.5, 1.2 Hz, 2H), 6.77 (ddd, *J* = 14.8, 11.0, 4.5 Hz, 4H).

Synthesis of compound *R/S-4*: Add 2, 3-difluoro-4-ethoxyphenylboronic acid (10.0 g, 50.0 mmol), 1-iodo-4 -(4-pentyl cyclohexyl) benzene (18.0 g, 50.0 mmol), tetra triphenylphosphine (0.5 g, 0.5 g) to a 250 mL single-mouth bottle. 0.5 mmol), 2.0 mol/L potassium carbonate aqueous solution (30 mL), 40 mL ethanol and 180 mL toluene, and the reaction system was reflowed at 80 °C for 24 h after replacing nitrogen gas (3 times). After cooling, the solvent was removed with a rotary evaporator, and after adding water, the solvent was extracted with dichloromethane (CH<sub>2</sub>Cl<sub>2</sub>) (3×60 mL), washed with water (3×80 mL), dried with anhydrous magnesium sulfate, filtered and collected for solvent removal. Using PE and CH<sub>2</sub>Cl<sub>2</sub> (volume ratio 1:2) as eluent, white solid was obtained by column chromatography, R-4 was 0.22 g, S-4 was 0.26 g, and the yield was 55% and 61%, respectively. *R***-4**: <sup>1</sup>H NMR (400 MHz, CD<sub>2</sub>Cl<sub>2</sub>)  $\delta$  (ppm) 8.18 (d, J = 9.0 Hz, 4H), 7.69 (ddd, J = 17.1, 13.0, 7.8 Hz, 8H), 7.56 (d, J = 8.9 Hz, 2H), 7.29 (dd, J = 8.1, 1.6 Hz, 12H), 7.24-7.09 (m, 18H), 7.01-6.91 (m, 8H), 6.88 (s, 4H), 6.82-6.65 (m, 10H), 4.07-3.91 (m, 24H), 2.40 (ddd, J = 12.1, 7.4, 2.8 Hz, 6H), 1.86-1.69 (m, 48H), 1.59-1.48 (m, 22H), 1.37 (dd, J = 17.4, 7.7 Hz, 12H), 1.30-1.09 (m, 58H), 1.03-0.92 (m, 12H), 0.81 (t, J = 7.0 Hz, 18H). TOF-MS (ESI) m/z calcd for  $C_{239}H_{268}F_{12}N_4O_{14}$ : 3648.77; [M+H]<sup>+</sup> found: 3649.222. S-4 : <sup>1</sup>H NMR (400 MHz,  $CD_2Cl_2$ )  $\delta$  (ppm) 8.18 (d, J = 8.9 Hz, 4H), 7.77-7.62 (m, 8H), 7.56 (d, J = 8.8 Hz, 2H), 7.29 (d, J = 6.8 Hz, 12H), 7.24-7.10 (m, 18H), 7.01-6.91 (m, 8H), 6.88 (s, 4H), 6.836.65 (m, 10H), 3.99 (ddt, J = 19.7, 13.2, 6.4 Hz, 24H), 2.40 (t, J = 11.1 Hz, 6H), 1.871.69 (m, 48H), 1.57-1.47 (m, 22H), 1.43-1.33 (m, 12H), 1.29-1.11 (m, 58H), 1.03-0.92 (m, 12H), 0.81 (t, J = 7.0 Hz, 18H). TOF-MS (ESI) *m/z* calcd for C<sub>239</sub>H<sub>268</sub>F<sub>12</sub>N<sub>4</sub>O<sub>14</sub>:
3648.77; [M+H]<sup>+</sup> found: 3649.235.



Figure S1. TGA curves of the emitters in  $N_2$  with the heating rate of 20 °C min<sup>-1</sup>.



Figure S2. CV curves of target compounds R/S-4 in CH<sub>2</sub>Cl<sub>2</sub> solution.



**Figure S3.** POM image of the SmA\* phase of *S*-4 on cooling at a) 182 °C and b) 155 °C. c) and d) SAXS pattern of *S*-4 on cooling process at 173 °C.



**Figure S4.** DSC curves of (a) *R*-4 and (b) *S*-4 with a heating/cooling rate of 10 °C min<sup>-1</sup>. The data show a small hysteresis in the onset temperatures on cooling for the transition between the SmA\* and the more ordered, lower-temperature mesophase, reflecting the more ordered nature of the latter.



Figure S5. Emission spectra of a) R-4 and b) S-4 in different solvents (10<sup>-5</sup> M).



Figure S6. Low temperature fluorescence (Fl) and phosphorescence (Ph) of a) R-4 and b) S-4 measured in toluene solution (10<sup>-5</sup> M)



Figure S7. Low temperature fluorescence (Fl) and phosphorescence (Ph) spectra of *S*-4 doped in mCP film



Figure S8. Transient PL decay curves of a) *R*-4 and b) *S*-4 in neat films with variable temperature.



Figure S9. CD spectrum and absorption spectrum of *R/S*-4 in neat films at room temperature.



Figure S10. a) Device architecture and b) materials used in the devices; c) and e) EQE-current density (inset: EL spectra of the devices) of R/S-4; d) and f) Current density–voltage–luminance curves of R/S-4.



Figure S11. The photoluminescence (PL) and absorption (UV) spectra of CzAcSF and *R/S*-4 in films.



Figure S12. EL spectra of the change in the concentration of *R*-4 when the sensitiser concentration was held at 30 wt%.



Figure S13. Transient PL decay curves of co-doped films of *R*-4 doped with different concentrations.



Figure S14. a) and b) EQE-current density (inset: EL spectra of the devices); c) and d) Current density–voltage–luminance curves of R/S-4.



Figure S15. Mechanism of sensitisation.



Figure S16. a) CPEL spectra and b)  $g_{EL}$  values of CPEL versus wavelength of (+)-*R*/ (-)-*S*-4 in device ( $\lambda_{ex} = 340 \text{ nm}$ ).

Compound	$\langle S_{l} H_{SOC} T_{l}\rangle$	$\langle S_1   H_{SOC}   T_2 \rangle$	$\langle S_1   H_{SOC}   T_3 \rangle$		
	(cm <sup>-1</sup> )	(cm <sup>-1</sup> )	(cm <sup>-1</sup> )		
<i>R</i> -4	0.552 cm	0.255	0.181		

Table S1. Calculated the SOC constant of the molecules.

#### Table S2. Thermal data of the emitters.

<i>T</i> /°C	Transition	$\Delta H/J \text{ g}^{-1}$
164.9	Cr-SmA*	2.0
184.8	SmA*-Iso	3.2
165.1	Cr-SmA*	1.8
184.3	SmA*-Iso	2.7
	<i>T/</i> °C 164.9 184.8 165.1 184.3	T/°C         Transition           164.9         Cr-SmA*           184.8         SmA*-Iso           165.1         Cr-SmA*           184.3         SmA*-Iso

Transition temperature and enthalpy measured during the second heating process at 20 °C/min.

Table S3. Summary of photophysical parameters for 5 wt% *R/S*-4 doped into mCP at various concentration

Compound	$ au_p/ oldsymbol{\Phi}_p$	$ au_d/ oldsymbol{\Phi}_d$	PLQY	k <sub>p</sub>	<i>k</i> <sub>d</sub>	<i>k</i> <sub>ISC</sub>	<i>k</i> <sub>rISC</sub>	<i>k</i> r	<i>k</i> <sub>nr</sub>
	(ns)/%	(µs)/%	(%)	$(10^7 s^{-1})$	(10 <sup>5</sup> s <sup>-1</sup> )	$(10^7 s^{-1})$	$(10^5 s^{-1})$	$(10^7 s^{-1})$	$(10^5 s^{-1})$
<i>R</i> -4	13.69/44.72	4.4/6.58	51.3	7.31	2.27	4.04	0.60	3.27	2.00
<i>S</i> -4	13.60/39.78	4.7/13.92	53.7	7.35	2.13	4.43	1.24	2.93	1.64
Notes: Massured In 5 wt % dened in mCP films									

$$k_{p} = \frac{1}{\tau_{p}} \qquad (1) \qquad k_{d} = \frac{1}{\tau_{d}} \qquad (2)$$

$$k_{ISC} = (1 - \Phi_{p})k_{p} \qquad (3) \qquad k_{rISC} = \frac{k_{p}k_{d}\Phi_{d}}{k_{ISC}\Phi_{p}} \qquad (4)$$

$$k_{r} = \frac{\Phi_{p}}{\tau_{p}} \qquad (5) \qquad k_{nr} = k_{d} - \Phi_{p}k_{rISC} \qquad (6)$$

Herein,  $\tau_p$  and  $\tau_d$  are the lifetime of prompt and delayed components.  $\Phi_p$  and  $\Phi_d$  are the prompt and delayed luminescence quantum efficiency, respectively. The  $k_p$  and  $k_d$  are the rate constant of prompt and delayed fluorescence.  $k_{ISC}$  is the rate constant of intersystem crossing, while  $k_{rISC}$  is the rate constant of reverse intersystem crossing between the  $S_1$  and  $T_1$ .  $k_r$  and  $k_{nr}$  are the radiative and nonradiative decay rate constant from  $S_1$  to  $S_0$ , respectively.

	Dopant	Von	L <sub>max</sub>	<b>CE</b> <sub>max</sub>	EOE	Peak	FWHM	CIE
		(V)	(cd/m2)	(cd/A)	LQLmax	(nm)		
	5 wt%	4.4	444.9	32.5	10.1	524	90.2	(0.31,0.56)
<i>R</i> -4	10 wt%	5.4	286.9	19.6	5.9	524	88	(0.31,0.57)
	15 wt%	5.6	441.4	17.5	5.2	528	89.2	(0.32,0.57)
	5 wt%	5.2	1007	20.1	6.1	528	91.0	(0.31,0.56)
<i>S</i> -4	10 wt%	5.2	372.9	18.2	5.4	528	90.3	(0.33,0.57)
	15 wt%	5.0	866.3	15.8	5.0	528	90.0	(0.31,0.56)

Table S4. Unsensitised device data for *R/S-4* 

(Device structure is ITO/ PEDOT:PSS/ mCP: x wt% *R***/S-4** (50 nm)/ TmPyPB (45 nm)/ LiF (0.5 nm)/ Al (120 nm))

Table S5. Sensitized device for changing the concentration of *R*-4

Dopant	Von	L <sub>max</sub>	<b>CE</b> <sub>max</sub>	EOE	Peak		CIE
	(V)	(cd/m2)	(cd/A)	EQE <sub>max</sub>	(nm)	r winw	
10 wt%	4.0	1998	19.46	6.61	508	100.5	(0.22,0.40)
20 wt%	4.0	2097	42.26	15.18	504	100.4	(0.21,0.38)
30 wt%	3.8	2238	51.74	18.27	504	99.5	(0.21,0.40)

(Device structure is ITO/ PEDOT:PSS/ mCP:x wt% CzAcSF: 1 wt% *R*-4 (50 nm)/ TmPyPB (45 nm)/ LiF (0.5 nm)/ Al (120 nm))

Table S6. Sensitised device data for *S*-4.

Device	Von	L <sub>max</sub>	<b>CE</b> <sub>max</sub>	EOE	Peak	FWHM	CIE
	(V)	(cd/m2)	(cd/A)	EQE <sub>max</sub>	(nm)		
<b>S4</b>	3.8	2737	58.3	19.7	508	95	(0.23,0.43)
<b>S5</b>	3.8	1223	54.8	19.8	504	97.6	(0.22,0.41)
<b>S6</b>	3.8	2341	60.3	21.2	504	98	(0.21,0.40)

(Device structure is ITO/ PEDOT:PSS/ mCP:30 wt% CzAcSF: x wt% *S*-4 (50 nm)/ TmPyPB (45 nm)/ LiF (0.5 nm)/ Al (120 nm) (where x wt%=0.5 wt%*S*-4 (S4),1 wt% *S*-4 (S5), and 1.5 wt%*S*-4 (S6)).

## 



-1.46

Figure S17. <sup>1</sup>H NMR spectrum of compound 1 in CD<sub>2</sub>Cl<sub>2</sub>













报告用户: CZCS 报告方法: 创索LC谱图报告 报告方法 ID: 2369 23694 页码: 1 (共计 1) 项目名称: CZCS OLED 打印日期: 2023/8/31 8:56:11 PRC

Figure S20. HPLC trace of *R*-4



Figure S21. <sup>1</sup>H NMR spectrum of *S*-4 in CD<sub>2</sub>Cl<sub>2</sub>



Figure S22. Mass spectrum of S-4



报告用户: CZCS 报告方法: 创素LC谱图报告 报告方法 ID: 2369 23697 页码: 1 (共计 1) 项目名称: CZCS OLED 打印日期: 2023/8/31 8:57:26 PRC

Figure S23. HPLC trace of S-4